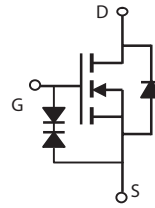
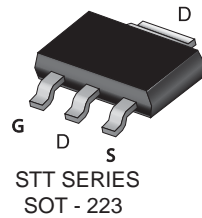


**N-Channel Logic Level Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
80V	1.4A	569 @ V _{GS} =10V
		674 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.

**ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)**

Symbol	Parameter	Limit	Units	
V _{DS}	Drain-Source Voltage	80	V	
V _{GS}	Gate-Source Voltage	±20	V	
I _D	Drain Current-Continuous ^{a d}	T _A =25°C	1.4	A
		T _A =70°C	1.1	A
I _{DM}	-Pulsed ^b	9.4	A	
P _D	Maximum Power Dissipation ^a	T _A =25°C	3	W
		T _A =70°C	1.9	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C	

THERMAL CHARACTERISTICS

R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	42	°C/W
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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	80			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =64V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±10	uA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	1.9	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =0.7A		455	569	m ohm
		V _{GS} =4.5V , I _D =0.65A		499	674	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =0.7A		2.4		S
DYNAMIC CHARACTERISTICS ^c						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V f=1.0MHz		150		pF
C _{OSS}	Output Capacitance			21		pF
C _{RSS}	Reverse Transfer Capacitance			13		pF
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =40V I _D =0.7A V _{GS} =10V R _{GEN} = 6 ohm		14.8		ns
t _r	Rise Time			14.7		ns
t _{D(OFF)}	Turn-Off Delay Time			133		ns
t _f	Fall Time			35		ns
Q _g	Total Gate Charge		V _{DS} =40V, I _D =0.7A, V _{GS} =10V		3	
Q _{gs}	Gate-Source Charge	V _{DS} =40V, I _D =0.7A, V _{GS} =10V		0.77		nC
Q _{gd}	Gate-Drain Charge			1		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =0.7A		0.84	1.2	V

Notes

- Surface Mounted on FR4 Board, t ≤ 10sec.
- Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Drain current limited by maximum junction temperature.

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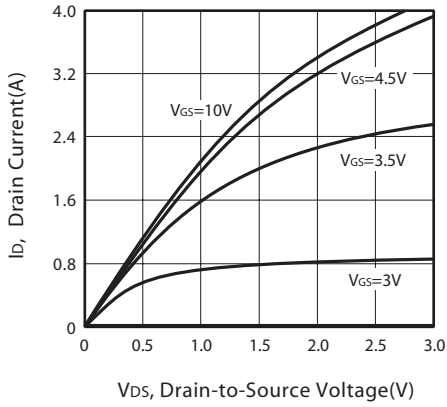


Figure 1. Output Characteristics

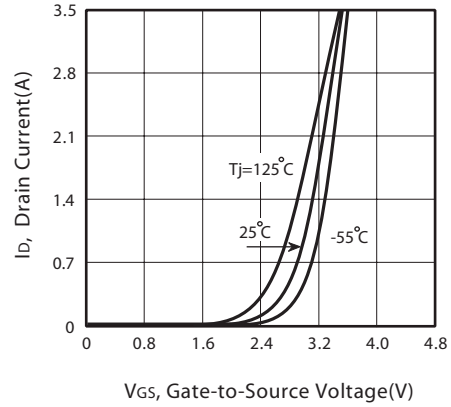


Figure 2. Transfer Characteristics

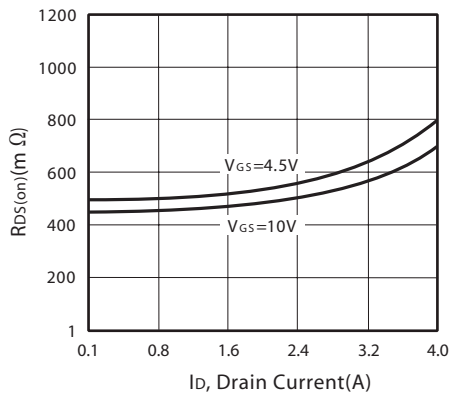


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

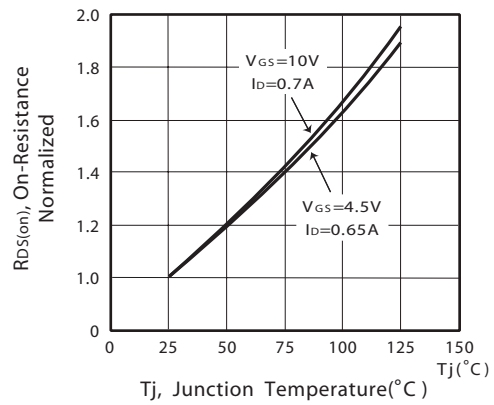


Figure 4. On-Resistance Variation with Drain Current and Temperature

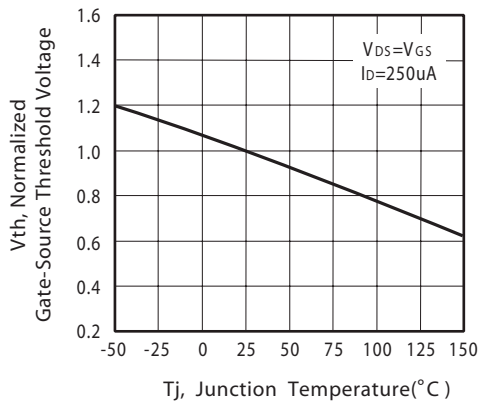


Figure 5. Gate Threshold Variation with Temperature

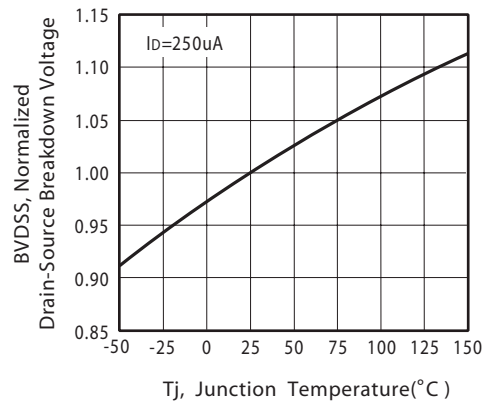


Figure 6. Breakdown Voltage Variation with Temperature

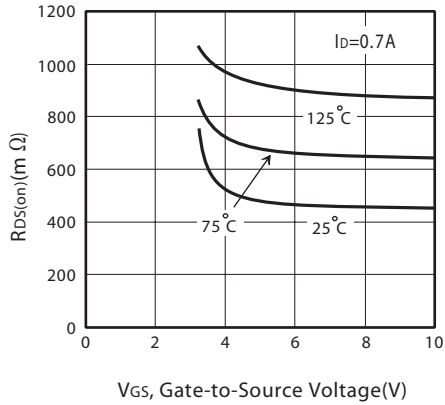


Figure 7. On-Resistance vs. Gate-Source Voltage

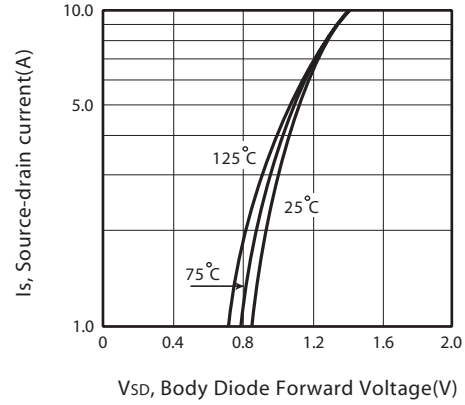


Figure 8. Body Diode Forward Voltage Variation with Source Current

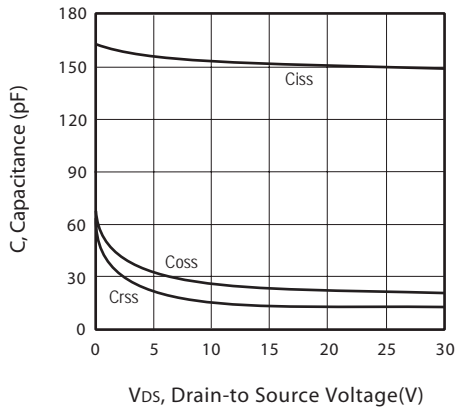


Figure 9. Capacitance

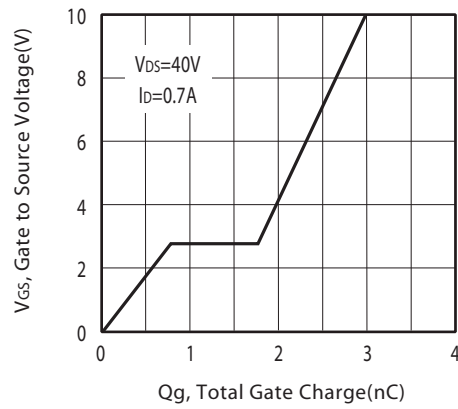


Figure 10. Gate Charge

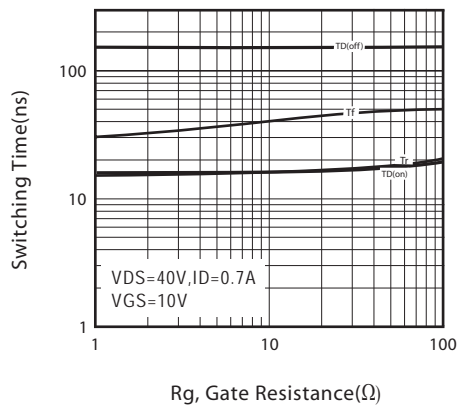


Figure 11. switching characteristics

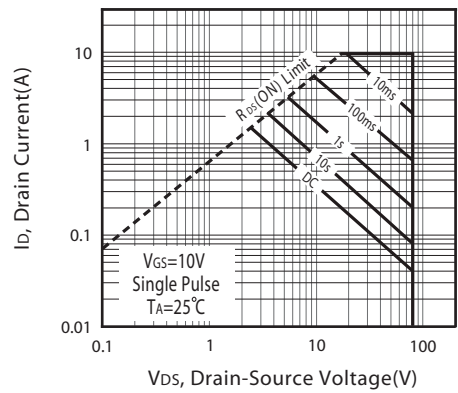


Figure 12. Maximum Safe Operating Area

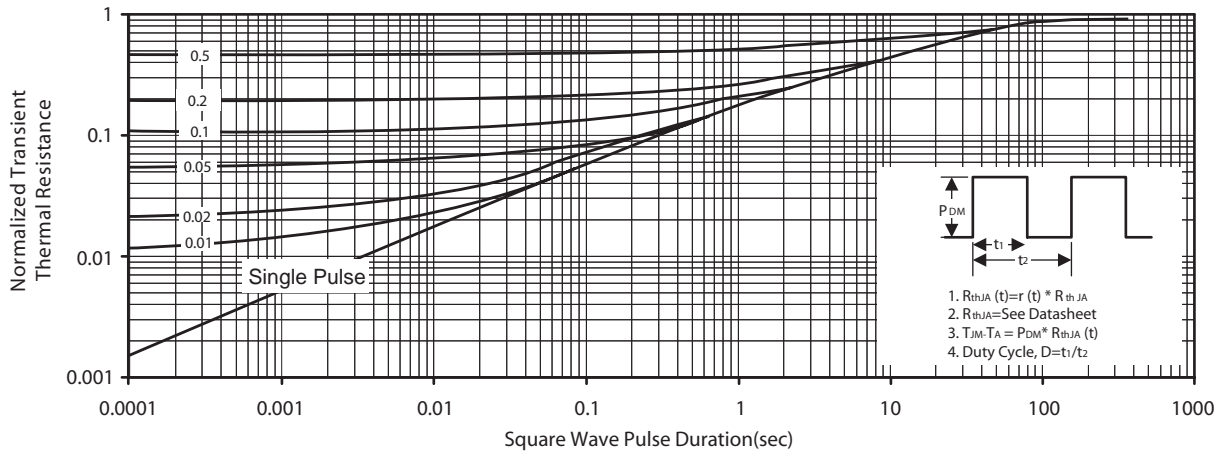
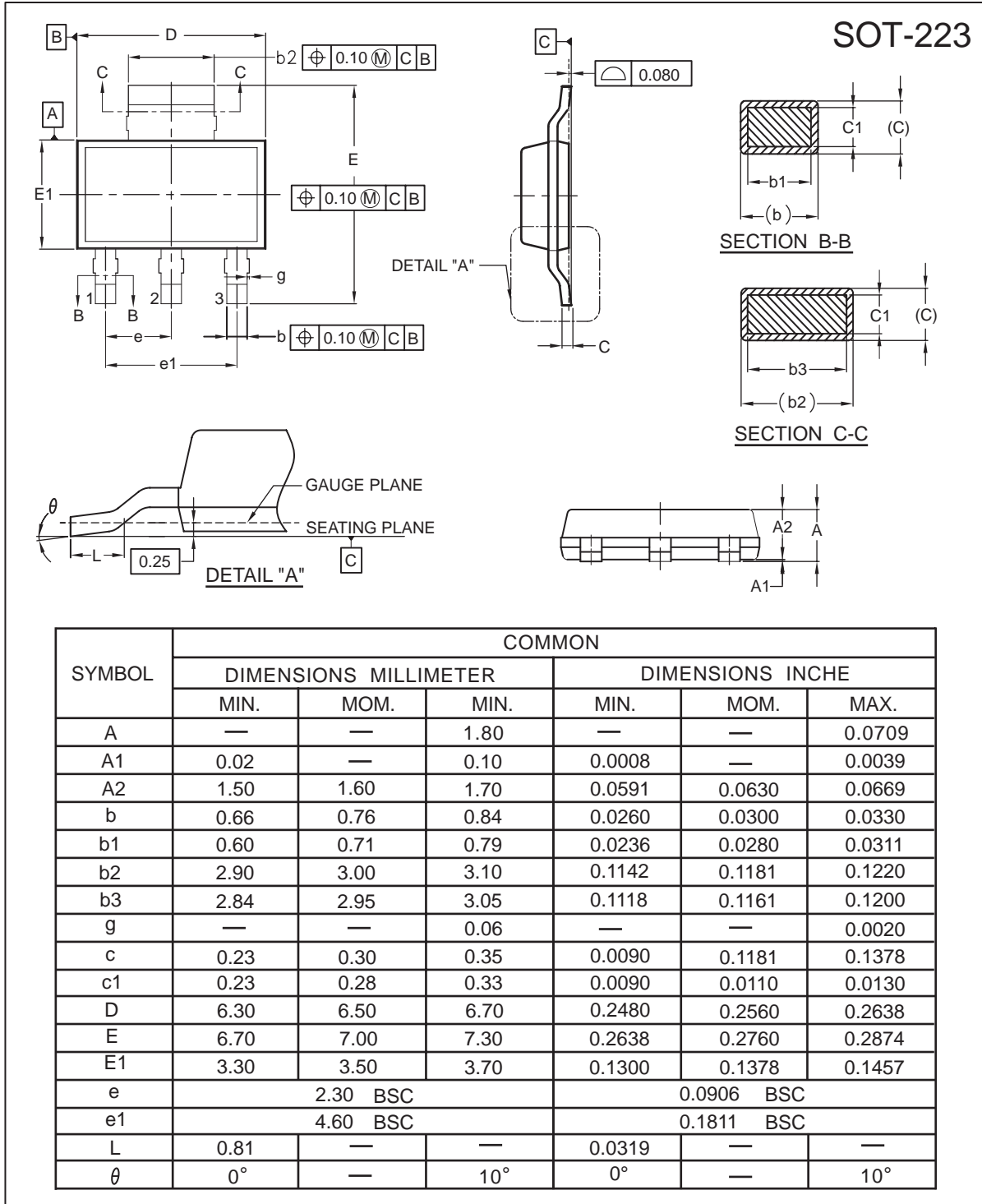


Figure 13. Normalized Thermal Transient Impedance Curve

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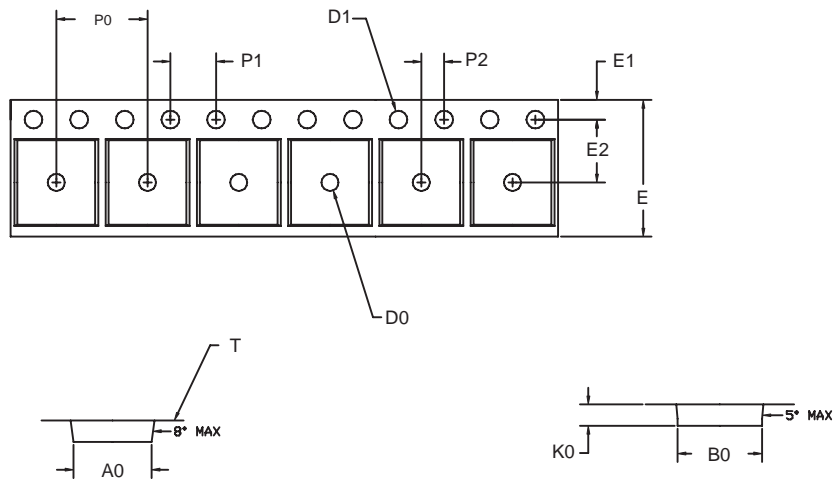
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SOT-223 Tape and Reel Data

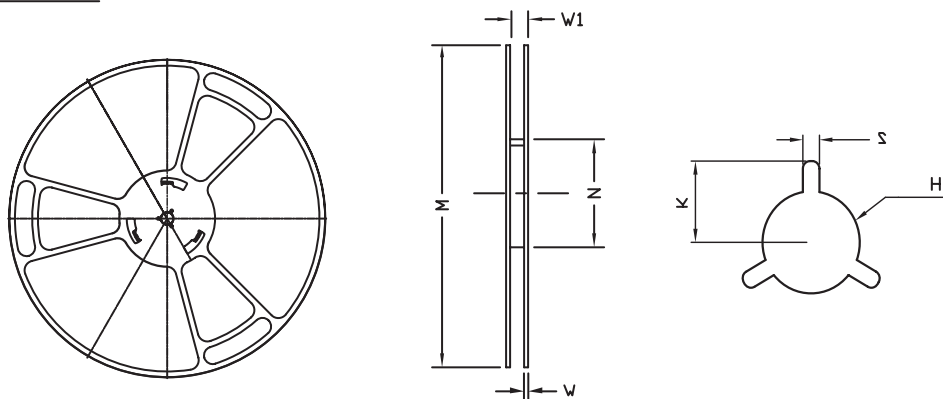
SOT-223 Carrier Tape



unit: mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
---	6.83 ±0.1	7.42 ±0.1	1.88 ±0.1	1.50 +0.25	1.60 +0.1	12.0 +0.3 -0.1	1.75 ±0.1	5.50 ±0.5	8.0 ±0.1	4.00 ±0.1	2.00 ±0.05	0.292 ±0.02

SOT-223 Reel



UNIT: mm

REEL SIZE	M	N	W	W1	H	K	S	G	R	V
φ 330 ± 0.5	---	φ 97.0 ± 1.0	2.2	13.0 + 1.5	φ 13.0 + 0.5 - 0.2	10.6	2.0 ± 0.5	---	---	---

TOP MARKING DEFINITION

